

## ULTRAFast SOFT RECOVERY RECTIFIER DIODE

### PRODUCT APPLICATIONS

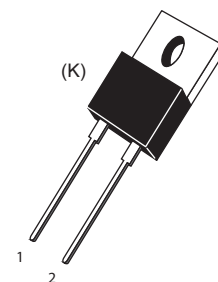
- Anti-Parallel Diode
  - Switchmode Power Supply
  - Inverters
- Free Wheeling Diode
  - Motor Controllers
  - Converters
  - Inverters
- Snubber Diode
- PFC

### PRODUCT FEATURES

- Ultrafast Recovery Times
- Soft Recovery Characteristics
- Popular TO-220 Package
- Low Forward Voltage
- Low Leakage Current
- Avalanche Energy Rated

### PRODUCT BENEFITS

- Low Losses
- Low Noise Switching
- Cooler Operation
- Higher Reliability Systems
- Increased System Power Density



1 - Cathode  
 2 - Anode  
 Back of Case - Cathode

### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

| Symbol         | Characteristic / Test Conditions                                                | APT30DQ100K(G) | UNIT             |
|----------------|---------------------------------------------------------------------------------|----------------|------------------|
| $V_R$          | Maximum D.C. Reverse Voltage                                                    | 1000           | Volts            |
| $V_{RRM}$      | Maximum Peak Repetitive Reverse Voltage                                         |                |                  |
| $V_{RWM}$      | Maximum Working Peak Reverse Voltage                                            |                |                  |
| $I_{F(AV)}$    | Maximum Average Forward Current ( $T_C = 102^\circ\text{C}$ , Duty Cycle = 0.5) | 30             | Amps             |
| $I_{F(RMS)}$   | RMS Forward Current (Square wave, 50% duty)                                     | 43             |                  |
| $I_{FSM}$      | Non-Repetitive Forward Surge Current ( $T_J = 45^\circ\text{C}$ , 8.3ms)        | 150            |                  |
| $E_{AVL}$      | Avalanche Energy (1A, 40mH)                                                     | 20             | mJ               |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range                                         | -55 to 175     | $^\circ\text{C}$ |
| $T_L$          | Lead Temperature for 10 Sec.                                                    | 300            |                  |

### STATIC ELECTRICAL CHARACTERISTICS

| Symbol   | Characteristic / Test Conditions          | MIN | TYP                                           | MAX  | UNIT          |
|----------|-------------------------------------------|-----|-----------------------------------------------|------|---------------|
| $V_F$    | Forward Voltage                           |     | $I_F = 30\text{A}$                            | 2.5  | Volts         |
|          |                                           |     | $I_F = 60\text{A}$                            | 3.06 |               |
|          |                                           |     | $I_F = 30\text{A}, T_J = 125^\circ\text{C}$   | 1.92 |               |
| $I_{RM}$ | Maximum Reverse Leakage Current           |     | $V_R = 1000\text{V}$                          | 100  | $\mu\text{A}$ |
|          |                                           |     | $V_R = 1000\text{V}, T_J = 125^\circ\text{C}$ | 500  |               |
| $C_T$    | Junction Capacitance, $V_R = 200\text{V}$ |     | 26                                            |      | pF            |

# DYNAMIC CHARACTERISTICS

APT30DQ100K(G)

| Symbol    | Characteristic                   | Test Conditions                                                              | MIN | TYP  | MAX | UNIT |
|-----------|----------------------------------|------------------------------------------------------------------------------|-----|------|-----|------|
| $t_{rr}$  | Reverse Recovery Time            | $I_F = 1A$ , $di_F/dt = -100A/\mu s$ , $V_R = 30V$ , $T_J = 25^\circ C$      | -   | 24   |     | ns   |
| $t_{rr}$  | Reverse Recovery Time            | $I_F = 30A$ , $di_F/dt = -200A/\mu s$<br>$V_R = 667V$ , $T_C = 25^\circ C$   | -   | 295  |     |      |
| $Q_{rr}$  | Reverse Recovery Charge          |                                                                              | -   | 440  |     | nC   |
| $I_{RRM}$ | Maximum Reverse Recovery Current |                                                                              | -   | 4    | -   | Amps |
| $t_{rr}$  | Reverse Recovery Time            | $I_F = 30A$ , $di_F/dt = -200A/\mu s$<br>$V_R = 667V$ , $T_C = 125^\circ C$  | -   | 330  |     | ns   |
| $Q_{rr}$  | Reverse Recovery Charge          |                                                                              | -   | 1550 |     | nC   |
| $I_{RRM}$ | Maximum Reverse Recovery Current |                                                                              | -   | 8    | -   | Amps |
| $t_{rr}$  | Reverse Recovery Time            | $I_F = 30A$ , $di_F/dt = -1000A/\mu s$<br>$V_R = 667V$ , $T_C = 125^\circ C$ | -   | 150  |     | ns   |
| $Q_{rr}$  | Reverse Recovery Charge          |                                                                              | -   | 2250 |     | nC   |
| $I_{RRM}$ | Maximum Reverse Recovery Current |                                                                              | -   | 25   |     | Amps |

# THERMAL AND MECHANICAL CHARACTERISTICS

| Symbol          | Characteristic / Test Conditions    | MIN | TYP  | MAX | UNIT         |
|-----------------|-------------------------------------|-----|------|-----|--------------|
| $R_{\theta JC}$ | Junction-to-Case Thermal Resistance |     |      | .80 | $^\circ C/W$ |
| $W_T$           | Package Weight                      |     | 0.07 |     | oz           |
|                 |                                     |     | 1.9  |     | g            |
| Torque          | Maximum Mounting Torque             |     |      | 10  | lb•in        |
|                 |                                     |     |      | 1.1 | N•m          |

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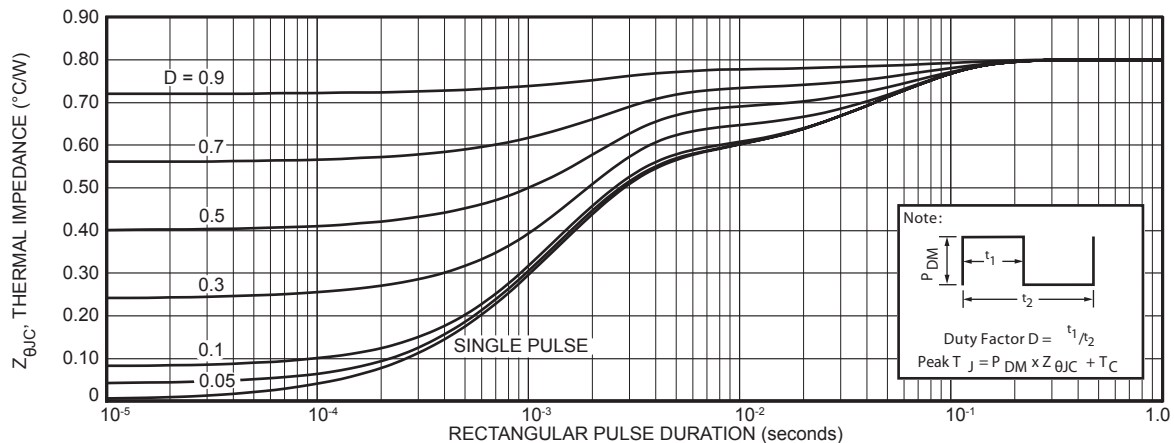


FIGURE 1. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

# TYPICAL PERFORMANCE CURVES

APT30DQ100K(G)

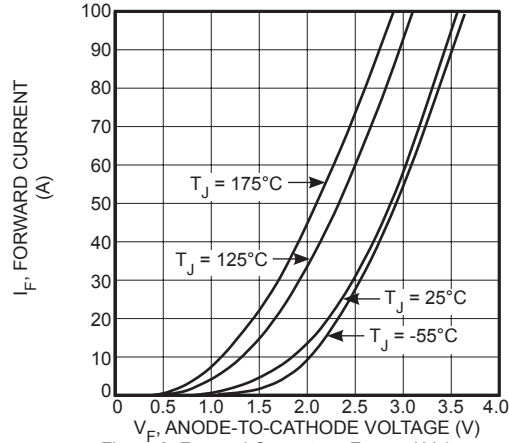


Figure 2. Forward Current vs. Forward Voltage

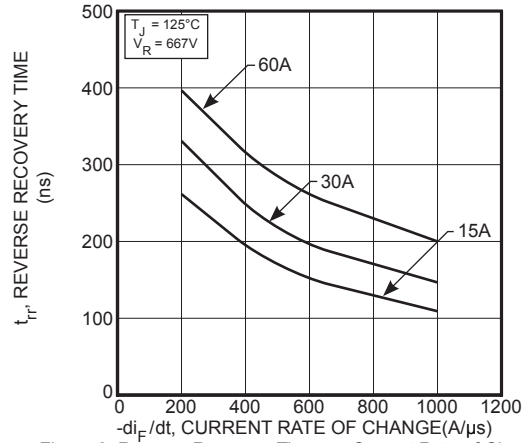


Figure 3. Reverse Recovery Time vs. Current Rate of Change

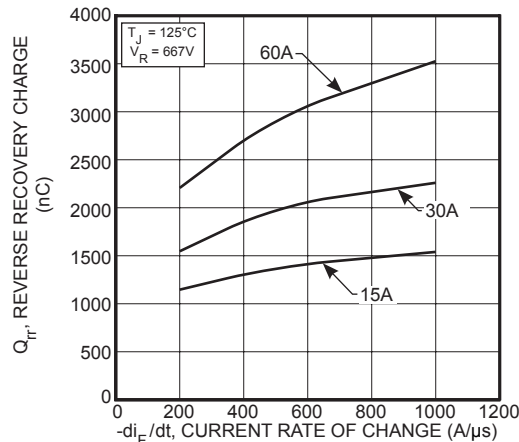


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

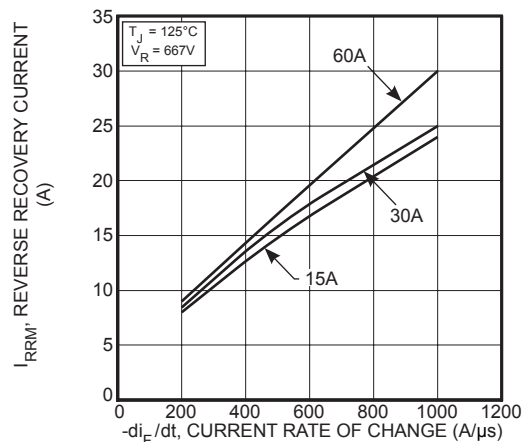


Figure 5. Reverse Recovery Current vs. Current Rate of Change

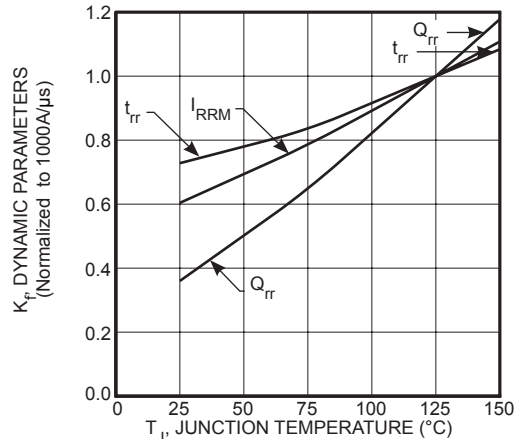


Figure 6. Dynamic Parameters vs. Junction Temperature

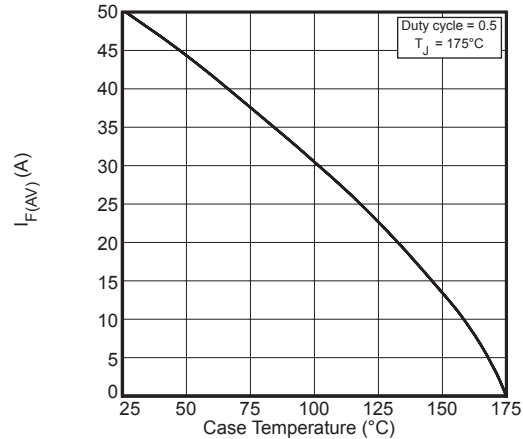


Figure 7. Maximum Average Forward Current vs. Case Temperature

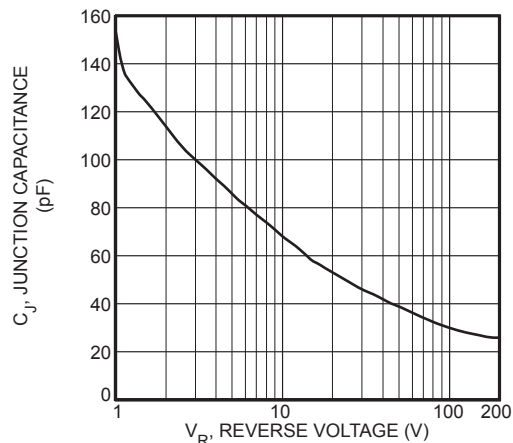


Figure 8. Junction Capacitance vs. Reverse Voltage

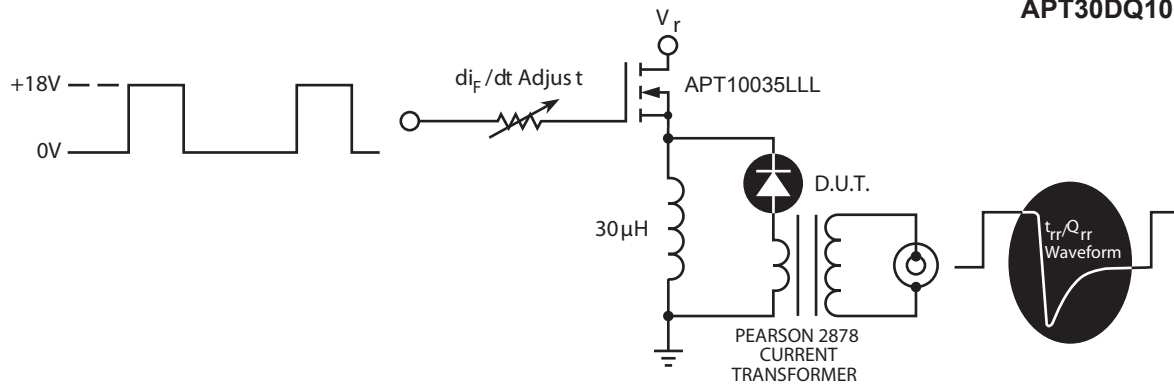


Figure 9. Diode Test Circuit

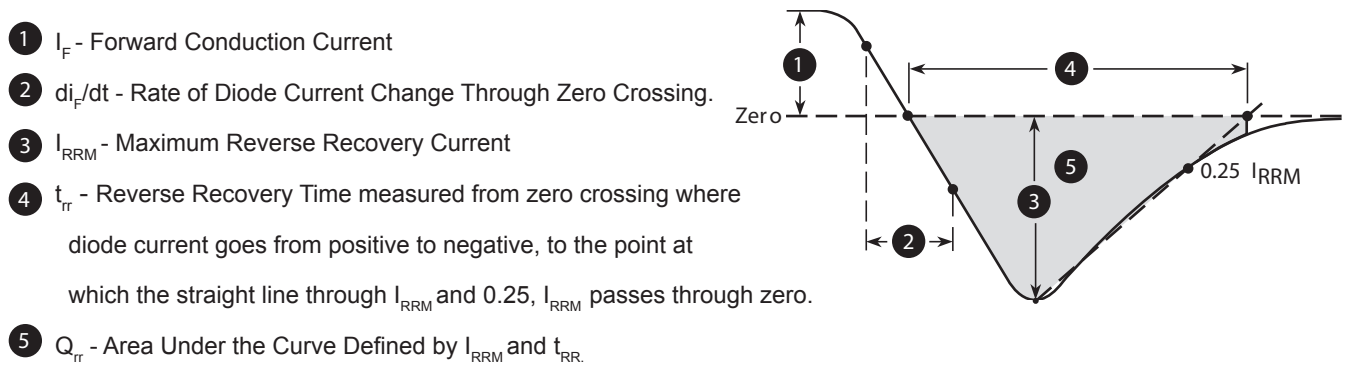
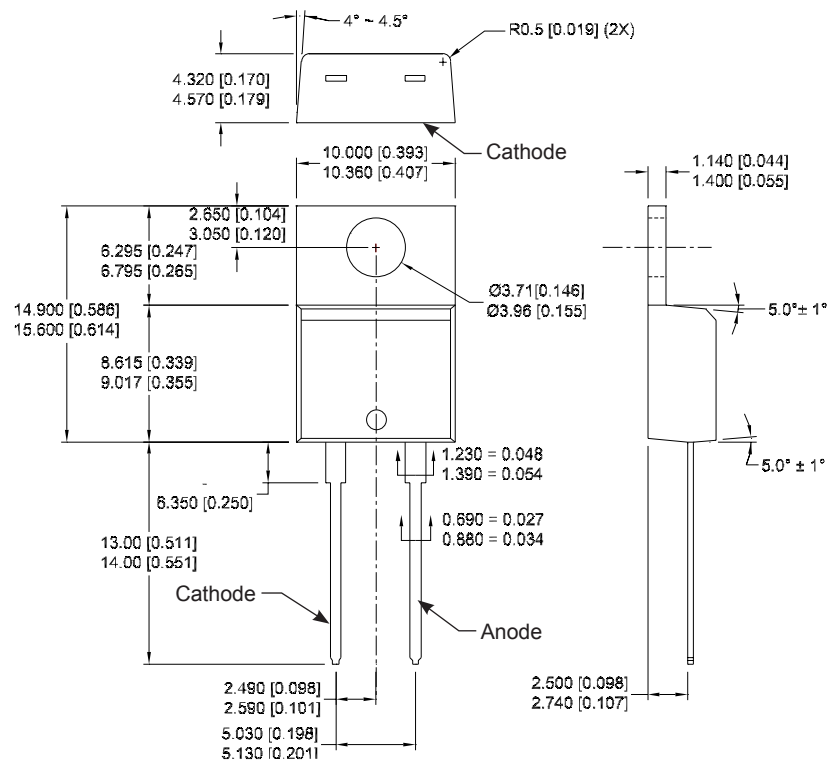


Figure 10. Diode Reverse Recovery Waveform Definition

## TO-220 (K) Package Outline

e3 100% Sn



Dimensions in millimeters and [inches]

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